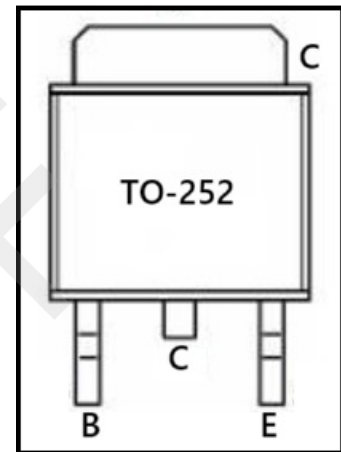


# MJD41C

- Complementary to: MJD42C
- Package: TO-252

## Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	$BV_{CBO}$	100	V
Collector-emitter voltage	$BV_{CEO}$	100	V
Emitter-base voltage	$BV_{EBO}$	5	V
Collector current	$I_{CM}$	6	A
Collector Power Dissipation	$P_C$	1.25	W
	$P_C(T_C=25^\circ)$	20	
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~+150	°C



## Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C=1mA, I_E=0$	100			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_C=30mA, I_B=0$	100			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E=1mA, I_C=0$	5			V
collector-emitter cut-off current	$I_{CEO}$	$V_{CE}=60V, I_B=0$			50	$\mu A$
emitter-base cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.5	mA
DC current gain	$H_{FE1}$	$V_{CE}=4V, I_C=3A$	15		75	
	$H_{FE2}$	$V_{CE}=4V, I_C=0.3A$	30			
collector-emitter saturation voltage	$V_{CESAT}$	$I_C=6A, I_B=0.6A$			1.5	V
Base-Emitter Saturation Voltage	$V_{BE(ON)}$	$V_{CE}=4V, I_C=6A$			2.0	V
Transition frequency	$f_T$	$V_{CE}=10V, I_C=500mA$	3			MHz